

TOSHIBA HIGH EFFICIENCY RECTIFIER SILICON EPITAXIAL TYPE

CRH01

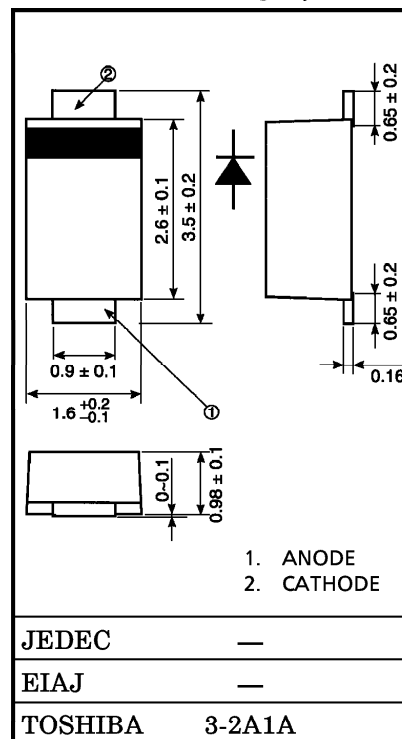
SWITCHING TYPE POWER SUPPLY APPLICATIONS

Unit in mm

- Repetitive Peak Reverse Voltage : $V_{RRM} = 200\text{ V}$
- Average Forward Current : $I_F(AV) = 1.0\text{ A}$
- Low Forward Voltage : $V_{FM} = 0.98\text{ V (Max.)}$
- Very Fast Reverse-Recovery Time : $t_{rr} = 35\text{ ns (Max.)}$
- Small & Thin Package : S-FLAT™
(Toshiba Package Name)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	200	V
Average Forward Current	$I_F(AV)$	1.0	A
Peak One Cycle Surge Forward Current (Non-Repetitive)	I_{FSM}	15 (50 Hz)	A
Junction Temperature	T_j	-40~150	°C
Storage Temperature Range	T_{stg}	-40~150	°C



Weight : 0.013 g

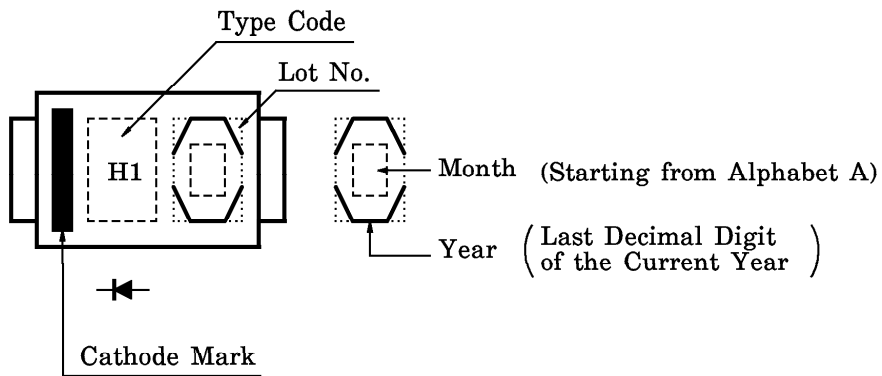
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$V_{FM}(1)$	$I_{FM} = 0.1\text{ A}$	—	0.71	—	V
	$V_{FM}(2)$	$I_{FM} = 0.7\text{ A}$	—	0.86	—	
	$V_{FM}(3)$	$I_{FM} = 1.0\text{ A}$	—	0.90	0.98	
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 200\text{ V}$	—	—	10	μA
Reverse Recovery Time	t_{rr}	$I_F = 1\text{ A}, di/dt = -30\text{ A}/\mu\text{s}$	—	—	35	ns
Forward Recovery Time	t_{fr}	$I_F = 1\text{ A}$	—	—	100	ns
Thermal Resistance	$R_{th}(j-a)$	On ceramic substrate	—	—	65	°C/W
		On glass-epoxy substrate	—	—	130	

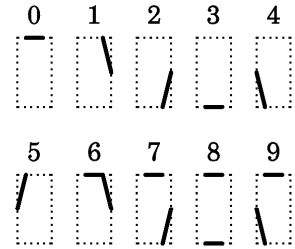
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MARKING



FOLLOWING INDICATES THE DATE OF MANUFACTURE



STANDARD SOLDERING PAD

Unit : mm

